

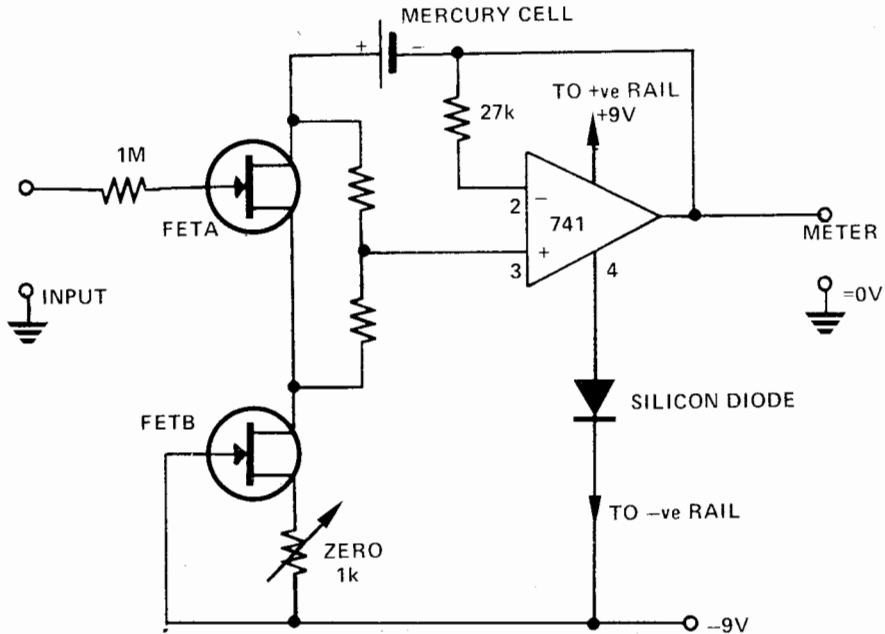
100,000 MEGOHM DC PROBE!

The input current of a junction FET, usually less than 1nA, flows out of the gate, and is constant at a particular temperature, provided the voltage across the device is constant. By making the gate positive to the source this leakage current can be made to flow back into the device, reducing the input current almost to zero.

FET A should be a low loss, low V_p device (ideally V_p should be about 0.5V). FET B must be somewhat higher but is less critical, the bargain pack is usually a good source of such devices. Forward bias should be about 150mV and current through the FETs about 400mA.

The mercury cell holds the voltage across the input FET constant at 1.5V (1.35V plus 150mV) and the silicon diode in the op amp's negative lead prevents the cell from discharging when the power is off.

By adjusting values in the potential



divider it is possible to achieve input currents within a few picoamps either way and to measure the voltage on a small capacitor without changing it.